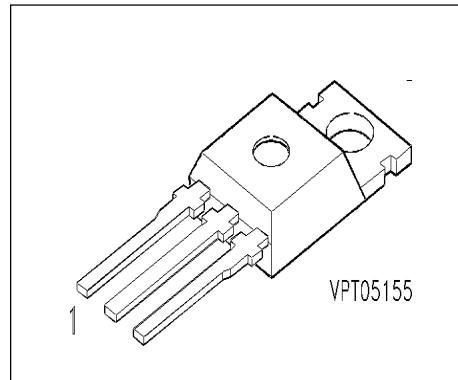


**IGBT**

- Low forward voltage drop
- High switching speed
- Low tail current
- Latch-up free
- Avalanche rated



Pin 1	Pin 2	Pin 3
G	C	E

Type	$V_{CE}$	$I_C$	Package	Ordering Code
SGP06N60	600V	6A	TO-220 AB	Q67041-A4709-A2

**Maximum Ratings**

Parameter	Symbol	Values	Unit
Collector-emitter voltage	$V_{CE}$	600	V
Collector-gate voltage	$V_{CGR}$	600	
$R_{GE} = 20 \text{ k}\Omega$	$V_{GE}$	$\pm 20$	
DC collector current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	$I_C$	14 6	A
Pulsed collector current, $t_p = 1 \text{ ms}$ $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	$I_{Cpuls}$	28 12	
Avalanche energy, single pulse $I_C = 6 \text{ A}$ , $V_{CC} = 50 \text{ V}$ , $R_{GE} = 25 \Omega$ $L = 500 \mu\text{H}$ , $T_j = 25^\circ\text{C}$	$E_{AS}$	9	
Power dissipation $T_C = 25^\circ\text{C}$	$P_{tot}$	70	W

*Preliminary data*
**Maximum Ratings**

Parameter	Symbol	Values	Unit
Chip or operating temperature	$T_j$	-55 ... + 150	°C
Storage temperature	$T_{stg}$	-55 ... + 150	
IEC climatic category, DIN IEC 68-1	-	55 / 150 / 56	-

**Thermal Resistance**

Thermal resistance, junction - case	$R_{thJC}$	$\leq 1.85$	K/W
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**Electrical Characteristics**, at  $T_j = 25$  °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**Static Characteristics**

Collector-emitter breakdown voltage $V_{GE} = 0$ V, $I_C = 0.5$ mA, $T_j = -55$ °C	$V_{(BR)CES}$	600	-	-	V
Gate threshold voltage $V_{GE} = V_{CE}$ , $I_C = 0.25$ mA, $T_j = 25$ °C $V_{GE} = V_{CE}$ , $I_C = 0.25$ mA, $T_j = 150$ °C	$V_{GE(th)}$	3 2	4 3	5 -	
Collector-emitter saturation voltage $V_{GE} = 15$ V, $I_C = 6$ A, $T_j = 25$ °C $V_{GE} = 15$ V, $I_C = 6$ A, $T_j = 150$ °C	$V_{CE(sat)}$	1.6 -	2 2.3	2.5 2.8	
Zero gate voltage collector current $V_{CE} = 600$ V, $V_{GE} = 0$ V, $T_j = 25$ °C $V_{CE} = 600$ V, $V_{GE} = 0$ V, $T_j = 150$ °C	$I_{CES}$	- -	- -	20 700	µA
Gate-emitter leakage current $V_{GE} = 25$ V, $V_{CE} = 0$ V	$I_{GES}$	-	-	100	nA

*Preliminary data*

**Electrical Characteristics**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**AC Characteristics**

Transconductance $V_{CE} = 20 \text{ V}, I_C = 6 \text{ A}$	$g_{fs}$	1.2	4.3	-	S
Input capacitance $V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	$C_{iss}$	-	350	435	pF
Output capacitance $V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	$C_{oss}$	-	40	50	
Reverse transfer capacitance $V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	$C_{rss}$	-	25	30	

*Preliminary data*

**Electrical Characteristics**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**Switching Characteristics, Inductive Load at  $T_j = 150^\circ\text{C}$**

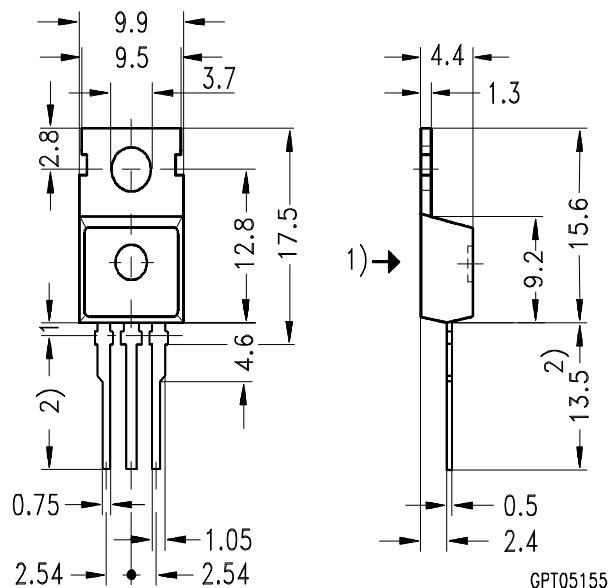
Turn-on delay time $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 6 \text{ A}$ $R_{Gon} = 50 \Omega$	$t_{d(on)}$	-	20	30	ns
Rise time $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 6 \text{ A}$ $R_{Gon} = 50 \Omega$	$t_r$	-	20	30	
Turn-off delay time $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 6 \text{ A}$ $R_{Goff} = 50 \Omega$	$t_{d(off)}$	-	250	380	
Fall time $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 6 \text{ A}$ $R_{Goff} = 50 \Omega$	$t_f$	-	70	105	
Total turn-on loss energy * $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 6 \text{ A}$ $R_{Gon} = 50 \Omega, T_j = 150^\circ\text{C}$	$E_{on}$	-	0.27	0.35	mJ
Total turn-off loss energy $V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 6 \text{ A}$ $R_{Goff} = 50 \Omega, T_j = 150^\circ\text{C}$	$E_{off}$	-	0.15	0.2	
Total Gate Charge $V_{CC} = 480 \text{ V}, V_{GE} = 15 \text{ V}, I_C = 6 \text{ A}$	$Q_{G(on)}$	-	32	48	nC

\* includes the reverse recovery losses caused by the FWD of the BUP410D

### Package Outlines

Dimensions in mm

Weight:



1) punch direction, burr max. 0.04

2) dip tinning

3) max. 14.5 by dip tinning press burr max. 0.05